

## **Erratum to: A new two-dimensional analytical subthreshold behavior model for submicron Triple Material Gate (TM) GaN MESFET**

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According to Prof. Faycal Djeflal, he is not a co-author of this paper. On his request, his authorship is withdrawn via this erratum. He had no contribution to the writing process of this paper. The authorship of this paper is attributed only to Dr. Nacereddine Lakhdar.

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